



### **IRFI830G Information**



For Reference Only

Part Number IRFI830G

Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 500V 3.1A TO220FP **Package** TO-220-3 Full Pack, Isolated Tab

Package TO-220-3 Full Pack, Isolated Tab
For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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### **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









# **IRFI830G Specifications**

Manufacturer Part Number         IRF1830G           Manufacturer         Vishay Siliconix           Category         Discrete Semiconductor Products		
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  TO-220-3 Full Pack, Isolated Tab  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  3.1A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  (10pF @ 25V  Vgs (Max)  +20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  1.5 Ohm @ 1.9A, 10V  Operating Temperature  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3 Full Pack, Isolated Tab	Manufacturer Part Number	IRFI830G
Package         TO-220-3 Full Pack, Isolated Tab           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         3.1A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         38nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         610pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         35W (Tc)           Rds On (Max) @ Id, Vgs         1.5 Ohm @ 1.9A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3           Full Pack, Isolated Tab	Manufacturer	Vishay Siliconix
PackageTO-220-3 Full Pack, Isolated TabSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C3.1A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds610pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)35W (Tc)Rds On (Max) @ Id, Vgs1.5 Ohm @ 1.9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Category	Discrete Semiconductor Products
Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         3.1A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         38nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         610pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         35W (Tc)           Rds On (Max) @ Id, Vgs         1.5 Ohm @ 1.9A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3 Full Pack, Isolated Tab		Transistors - FETs, MOSFETs - Single
FET Type  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  3.1A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  1.5 Ohm @ 1.9A, 10V  Operating Temperature  Supplier Device Package  Package / Case  N-Channel  MOSFET (Metal Oxide)  MOSFET (Metal Oxide)  500V  3.1A (Tc)  3.1A (Tc)  3.1A (Tc)  3.1A (Tc)  3.1A (Tc)  3.1A (Tc)  4V @ 250µA  4V @ 250µA  610pF @ 25V  50V  50V  50V  50V  50V  50V  50V	Package	TO-220-3 Full Pack, Isolated Tab
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C3.1A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds610pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)35W (Tc)Rds On (Max) @ Id, Vgs1.5 Ohm @ 1.9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Series	-
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Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  +20V  FET Feature  - Power Dissipation (Max)  35W (Tc)  Rds On (Max) @ Id, Vgs  1.5 Ohm @ 1.9A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3 Full Pack, Isolated Tab	Current - Continuous Drain (Id) @ 25°C	3.1A (Tc)
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Vgs (Max) ±20V  FET Feature -  Power Dissipation (Max) 35W (Tc)  Rds On (Max) @ Id, Vgs 1.5 Ohm @ 1.9A, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220-3  Package / Case TO-220-3 Full Pack, Isolated Tab	Gate Charge (Qg) (Max) @ Vgs	38nC @ 10V
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Rds On (Max) @ Id, Vgs1.5 Ohm @ 1.9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3 Full Pack, Isolated Tab	Power Dissipation (Max)	35W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Rds On (Max) @ Id, Vgs	1.5 Ohm @ 1.9A, 10V
Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack, Isolated Tab	Mounting Type	Through Hole
	Supplier Device Package	TO-220-3
Report errors?	Package / Case	TO-220-3 Full Pack, Isolated Tab
		Report errors?

### **IRFI830G Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **IRFI830G Payment Methods**





















## **IRFI830G Shipping Methods**













If you have any question about IRFI830G, please do not hesitate to contact us!

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